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(54) Title: SILICON POLISHING COMPOSITIONS WITH HIGH RATE AND LOW DEFECTIVITY

(57) Abstract: The invention relates to a chemical-mechanical polishing composition comprising silica, one or more organic carboxylic acids or salts thereof, one or more polysaccharides, one or more bases, optionally one or more surfactants and/or polymers, optionally one or more reducing agents, optionally one or more biocides, and water, wherein the polishing composition has an alkaline pH. The polishing composition exhibits a high removal rate and low particle defects and low haze. The invention further relates to a method of chemically-mechanically polishing a substrate using the polishing composition described herein.

